*Work supported by the U.S. Air Force Office of Scientific Research under Grant No. AF-AFOSR 1257–67.

[1]B. N. N. Achar and G. R. Barsch, Phys. Rev. 188, 1356 (1969).

[2]B. N. N. Achar and G. R. Barsch, Phys. Rev. 188, 1361 (1969).

[3]J. L. Synge, J. Math. and Phys. 35, 323 (1957).

[4]T. E. Feuchtwang, Phys. Rev. 155, 731 (1967).

[5]In anisotropic elastic continua, three values of k_3 are needed to satisfy the boundary conditions.

[6]Exceptions to this rule are certain unrealistically simple models, e.g., those used by Lengeler and Ludwig and by Takeno (see Ref. 1).

[7]S. Y. Tong and A. A. Maradudin, Phys. Rev. 181, 1318 (1969).

[8]See Table V of Ref. 2 for $\vec{k}_p$ along the [100] axis with magnitude $0.3\times 2\pi/r_0$.

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ERRATA

High-Frequency de Haas-van Alphen Oscillations in Aluminum,
[Phys. Rev. B 2, 298 (1970)]. The κ in the argument of the Bessel function, $J_2(2\pi F\kappa h_m/H^2)$, on p. 305 has the value 0.43 instead of 0.23.

Free-Carrier Radiation Peak in GaAs Due to Valence-Band Maxima Arising from Terms Linear in k, M. A. Gilleo and P. T. Bailey [Phys. Rev. 187, 1181 (1969)]. The photoluminescence line at 1.520 eV associated in this paper with valence-band maxima arising from terms linear in k in addition to the other two lines in Fig. 1 have been found to be grating ghosts of stronger lines in the spectra. {See the following erratum [Phys. Rev. B 3, 3581 (1971)].}

Free-Carrier and Exciton Recombination Radiation in GaAs, M. A. Gilleo, P. T. Bailey, and D. E. Hill [Phys. Rev. 174, 898 (1968)]. The following photoluminescence lines reported in this paper have been found to be grating ghosts of stronger lines in the spectrum: (i) the line at 1.5202 eV associated in this paper with free-carrier recombination, (ii) the line at 1.5193 eV associated with "$n=2$" exciton recombination, and (iii) the pair of lines (Fig. 4) at 1.518 and 1.506 eV related to the neutral zinc exciton line. In addition, the triplet shown in Fig. 10 became a doublet, and the doublet shown in Fig. 6 became a single line after this sample was etched. We believe the etch relieved some residual strain in the as-grown sample. Confirmation of this was obtained by examining other samples. The rest of the features of the spectra reported in this paper have been confirmed using different gratings.

Theory of Interband Raman Scattering in Semiconductors in Magnetic Fields, R. F. Wallis and D. L. Mills [Phys. Rev. B 2, 3312 (1970)]. The algebraic sign of the terms involving m_v^* in Eq. (7) should be changed from plus to minus. In Eq. (8), the factor

$$\left(\frac{\omega_c^2}{\omega_1^2-\omega_c^2}+\frac{\omega_c^2}{\omega_0^2-\omega_c^2}\right)$$

should be replaced by the factor

$$\left(\frac{\omega_c\omega_1}{\omega_1^2-\omega_c^2}-\frac{\omega_c\omega_0}{\omega_0^2-\omega_c^2}\right)^2 .$$

For PbTe at 50 kG with YAG:Nd excitation, the scattering efficiency near resonance is little affected by this correction, but far from resonance it is increased by about two orders of magnitude over that shown in the right-hand side of Fig. 2. The possibility of experimental observation of the scattering far from resonance is thus significantly enhanced. We thank Dr. Y. Yafet for calling this correction to our attention.